RENESAS HD74LV4066A

Quad. Analog Switches / Quad. Multiplexers

REJ03D0340-0400Z (Previous ADE-205-285B (Z)) Rev.4.00 Jul. 21, 2004

Description

The HD74LV4066A handles both analog and digital signals, and enables signals of either type with amplitudes of up to 5.5 V (peak) to be transmitted in either direction (at $V_{CC} = 0$ V to 5.5 V).

Each switch section has its own enable input control (C). A high-level voltage applied to C turns on the associated switch section.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

Features

- $V_{CC} = 2.0 \text{ V}$ to 5.5 V operation
- All control inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV4066AFPEL	SOP–14 pin (JEITA)	FP–14DAV	FP	EL (2,000 pcs/reel)
HD74LV4066ARPEL	SOP-14 pin (JEDEC)	FP–14DNV	RP	EL (2,500 pcs/reel)
HD74LV4066ATELL	TSSOP-14 pin	TTP-14DV	Т	ELL (2,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

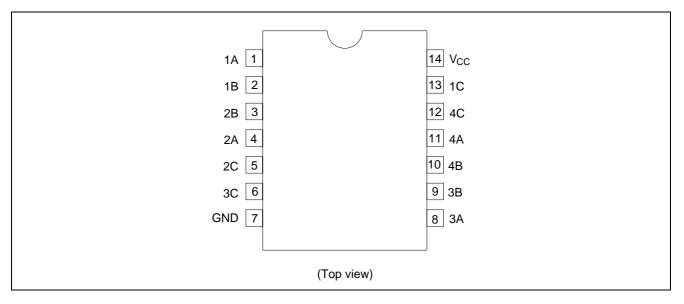
Function Table

Control	Switch
L	OFF
Н	ON
Note: H: High level	

L: Low level



Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{CC}	–0.5 to 7.0	V	
Input voltage range*1	VI	–0.5 to 7.0	V	
Output voltage range*1, 2	Vo	-0.5 to V _{CC} + 0.5	V	Output: H or L
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	l _{ок}	±50	mA	$V_0 < 0$ or $V_0 > V_{CC}$
Continuous output current	lo	±25	mA	$V_0 = 0$ to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	±50	mA	
Maximum power dissipation at	PT	785	mW	SOP
Ta = 25°C (in still air)* ³		500		TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.

2. This value is limited to 5.5 V maximum.

3. The maximum package power dissipation was calculated using a junction temperature of 150°C.



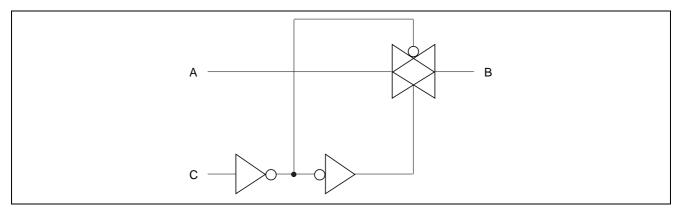
Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	Vcc	2.0* ¹	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	V _{I/O}	0	V _{CC}	V	
Input transition rise or fall rate	$\Delta t/\Delta v$	0	200	ns/V	V_{CC} = 2.3 to 2.7 V
		0	100		V_{CC} = 3.0 to 3.6 V
		0	20		V_{CC} = 4.5 to 5.5 V
Operating free-air temperature	Та	-40	85	°C	

Notes: Unused or floating control inputs must be held high or low.

1. With the supply voltage at or around 2 V, the analog switch on-state resistance loses linearity significantly. It is recommended that only digital signals be transmitted at these low supply voltages.

Logic Diagram



DC Electrical Characteristics

			Ta =	25°C		Ta = -40 t	o 85°C			
Item	Symbol	V _{cc} (V)	Min	n Typ Max Min Max		Max	Unit	Test Conditions		
Input voltage	VIH	2.0	_	_	_	1.5		V	Control input only	
		2.3 to 2.7	_	_		$V_{CC}\!\times\!0.7$	_	_		
		3.0 to 3.6		_	_	$V_{CC}\!\times\!0.7$	_			
		4.5 to 5.5	_	_		$V_{CC}\!\times\!0.7$	_	_		
	VIL	2.0		_	_	_	0.5			
		2.3 to 2.7	_	_		_	$V_{CC} imes 0.3$	_		
		3.0 to 3.6		_	_	_	$V_{CC}\!\times\!0.3$			
		4.5 to 5.5	_	_	_	_	$V_{CC}\!\times\!0.3$	_		
On-state switch	Ron	2.3	—	60	180	_	225	Ω	$V_{IN} = V_{CC} \text{ or } GND$	
resistance		3.0	_	50	150	_	190		$V_{C} = V_{IH}$	
		4.5		40	75		100	_	$I_T = 1 \text{ mA}$	
Peak on resistance	R _{ON (P)}	2.3	_	250	500	_	600	Ω	$V_{IN} = V_{CC}$ to GND	
		3.0	_	100	180	_	225		$V_{C} = V_{IH}$	
		4.5	_	50	100	_	125		$I_T = 1 \text{ mA}$	
Difference of on-state	ΔR_{ON}	2.3	_	20	30	_	40	Ω	$V_{IN} = V_{CC}$ to GND	
resistance between		3.0	_	10	20	_	30		$V_{C} = V_{IH}$	
switches		4.5	_	7	15	_	20		$I_T = 1 \text{ mA}$	
Off-state switch leakage current	Is (OFF)	5.5			±0.1	_	±1.0	μΑ	$\label{eq:VIN} \begin{split} V_{IN} &= V_{CC}, \\ V_{OUT} &= GND \text{ or } \\ V_{IN} &= GND, \\ V_{O} &= V_{CC}, \ V_{C} &= V_{IL} \end{split}$	
On-state switch leakage current	ls (ON)	5.5			±0.1	_	±1.0	μA	$V_{IN} = V_{CC} \text{ or } GND$ $V_C = V_{IH}$	
Input current	I _{IN}	0 to 5.5	_	_	±0.1	_	±1.0	μA	V_{IN} = 5.5 V or GND	
Quiescent supply current	lcc	5.5	_		_	_	20	μA	$V_{IN} = V_{CC} \text{ or } GND$	

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.



Switching Characteristics

										V_{CC}	$= 2.5 \pm 0.2 \text{ V}$
		Ta = 2	25°C		Ta = –	40 to 85°C				FROM	то
ltem	Symbol	Min	Тур	Max	Min	Max	Unit	Test Cond	ditions	(Input)	(Output)
Propagation	t _{PLH}	_	2.0	10.0	_	16.0	ns	C _L = 15 pF	-	A or B	B or A
delay time	t _{PHL}	—	5.0	12.0	—	18.0	_	$C_L = 50 \text{ pF}$	-	_	
Enable time	t _{zH}	_	6.0	15.0	_	20.0	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$	С	A or B
	t _{ZL}	_	8.0	25.0	_	32.0	_		$C_L = 50 \text{ pF}$	-	
Disable time	t _{HZ}	_	7.0	15.0	_	23.0	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$	С	A or B
	t _{LZ}	_	11.0	25.0	_	32.0	_		$C_L = 50 \text{ pF}$	_	

$V_{CC}=3.3\pm0.3~V$

		Ta = 2	25°C		Ta = –	40 to 85°C				FROM	то
ltem	Symbol	Min	Тур	Max	Min	Max	Unit	Test Cond	ditions	(Input)	(Output)
Propagation	t _{PLH}	_	1.5	6.0	_	10.0	ns	C _L = 15 pF	-	A or B	B or A
delay time	t _{PHL}	_	4.0	9.0	_	12.0		$C_{L} = 50 pF$	=	-	
Enable time	t _{zH}		4.0	11.0	_	15.0	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$	С	A or B
	t _{ZL}	_	6.0	18.0		22.0	-		$C_L = 50 \text{ pF}$	_	
Disable time	t _{HZ}		5.0	11.0	_	15.0	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$	С	A or B
	t _{LZ}		8.0	18.0		22.0	_		$C_L = 50 \text{ pF}$	_	

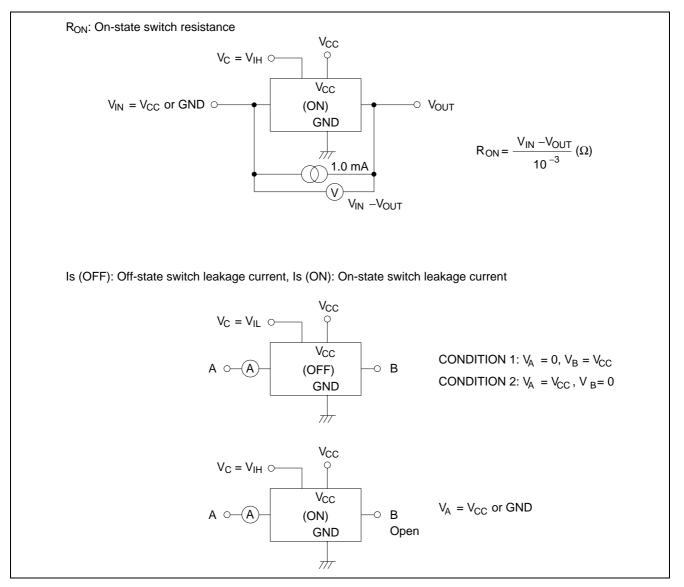
$V_{CC}=5.0\pm0.5~V$

		Ta = 25°C Ta = -40 to 85°C							FROM	то	
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Cond	litions	(Input)	(Output)
Propagation	t _{PLH}		1.0	4.0		7.0	ns	C∟ = 15 pF	-	A or B	B or A
delay time	t _{PHL}	_	3.0	6.0	_	8.0	_	C∟ = 50 pF	-	-	
Enable time	t _{ZH}	_	3.0	7.0	_	10.0	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$	С	A or B
	t _{ZL}	_	5.0	12.0	_	16.0	-		$C_L = 50 \text{ pF}$	_	
Disable time	t _{HZ}	_	4.0	7.0	_	10.0	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$	С	A or B
	t _{LZ}		6.0	12.0	_	16.0	_		$C_L = 50 \text{ pF}$	_	

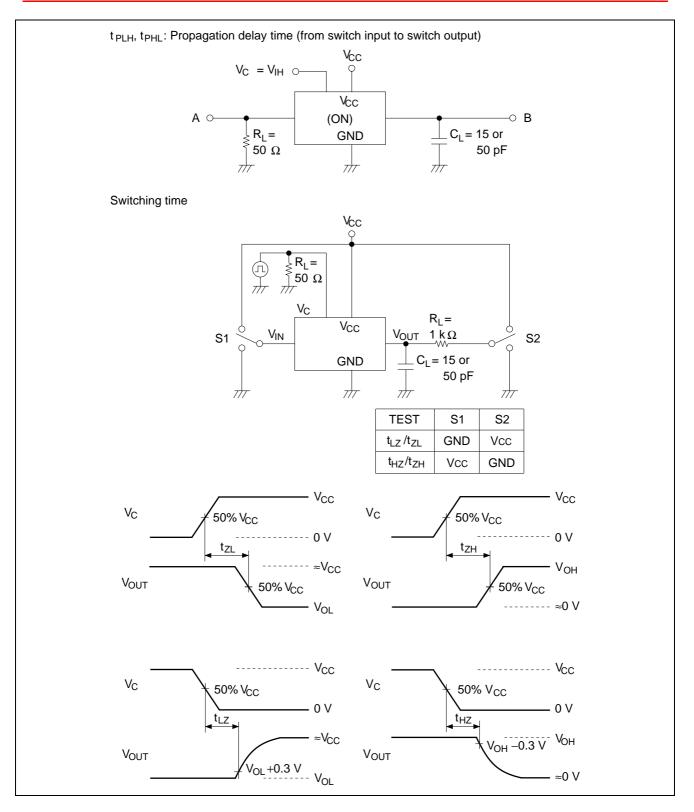
Switching Characteristics (Cont.)

			Ta = 2	25°C				FROM	то
Item	Symbol	V _{cc} (V)	Min	Тур	Мах	Unit	Test Conditions	(Input)	(Output)
Control input capacitance	C _{IC}		—	3.5		pF			
Switch terminal capacitance	C _{I/O}	_	_	6.0	—	pF			
Feedthrough capacitance	CT			0.5		pF			
Power dissipation capacitance	C _{PD}	—	—	4.0	—	pF			
Frequency		2.3	—	30.0	—	MHz	$C_L = 50 \text{ pF}, \text{ R}_L = 600 \Omega$	A or B	B or A
response		3.0	_	35.0		_	Adjust f _{in} voltage to obtain 0 dBm		
(Switch ON)		4.5	_	50.0	_		at output when f_{in} is 1 MHz (sine wave). Increase f_{in} frequency until the dB-meter reads –3dBm. 20 log (V _O /V _I) = –3 dBm		
Crosstalk		2.3	_	-45.0	_	dB	$C_L = 50 \text{ pF}, \text{ R}_L = 600 \Omega$	A or B	B or A
(Between any		3.0	_	-45.0	_	_	Adjust fin voltage to obtain 0 dBm		
switches)		4.5	—	-45.0	—		at input when f _{in} is 1 MHz (sine wave).		
Crosstalk		2.3	_	15.0		mV	C_L = 50 pF, R_L = 600 Ω	С	A or B
(Control input		3.0	—	20.0	—	_	Adjust R_L value to obtain		
to signal output)		4.5	—	50.0	—		0 A at I _{IN/OUT} when f _{in} is 1 MHz (square wave).		
Feedthrough		2.3	_	-40.0	_	dB	C_L = 50 pF, R_L = 600 Ω	A or B	B or A
attenuation		3.0	—	-40.0	—	_	Adjust f _{in} voltage to obtain 0 dBm at input when f _{in} is 1 MHz (sine wave).		
(Switch OFF)		4.5	—	-40.0	—				
Sine-wave		2.3	_	0.1		%	$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$	A or B	B or A
distortion		3.0	—	0.1	—	_	$f_{IN} = 1 \text{ kHz}$ (sine wave)		
		4.5		0.1					

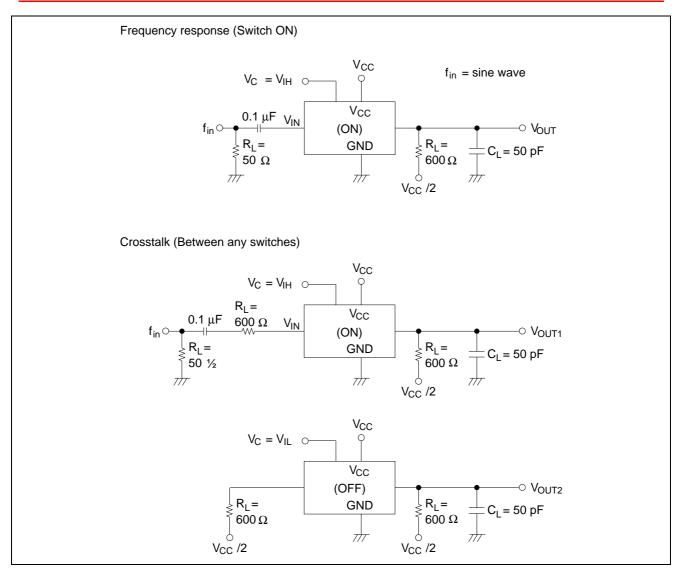
Test Circuits

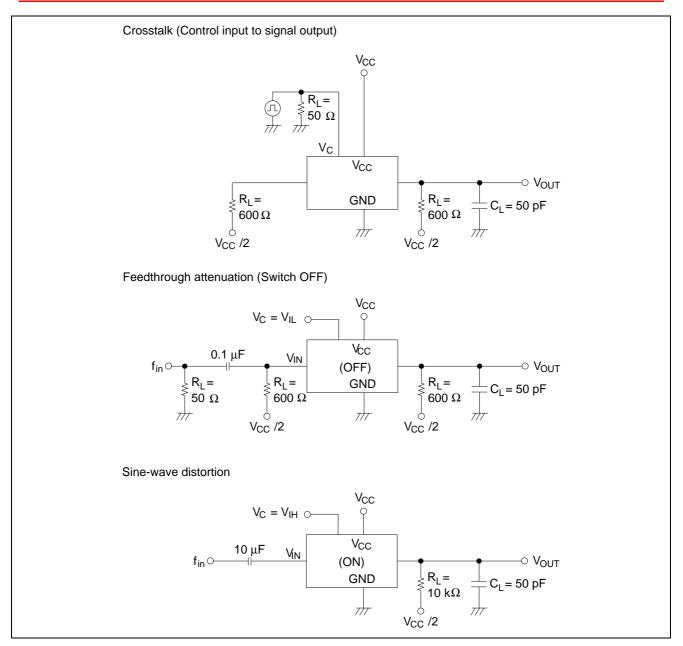




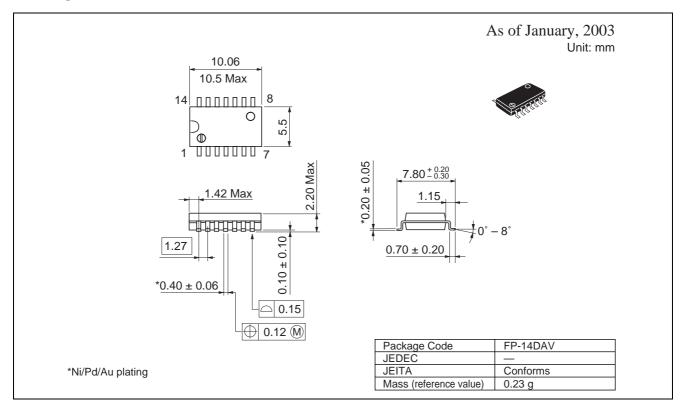


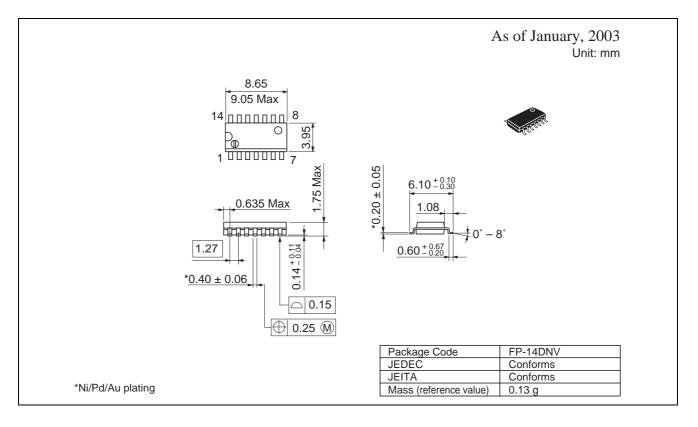
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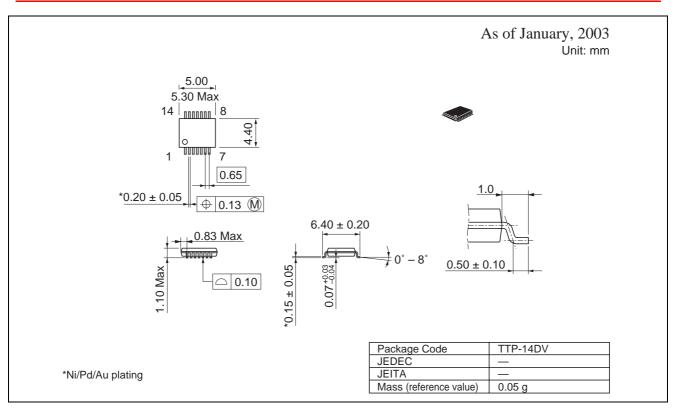


Package Dimensions









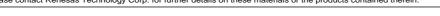


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